18. (Amended) A device according to claim 17, wherein the first electrode is a gate electrode.

19. (Amended) A device according to claim 17, wherein a storage capacitor is formed by the second semiconductor layer, the second electrode, and the first insulating film.

21. (Amended) A device according to claim 17, wherein the gate wiring comprising an element selected from the group consisting of polysilicon doped with an impurity element which imparts one conductivity, W, WSix, Al, Cu, Ta, Cr, and Mo as its main constituent, and a lamination film of the elements.

Please add new claims 48-75 as follows:

--48. A semiconductor device comprising:

a first semiconductor layer and a second semiconductor layer on an insulating surface;

a first insulating film on the first semiconductor layer and on the second semiconductor layer;

first and second electrodes on the first insulating film, the first electrode overlapping the first semiconductor layer and the second electrode overlapping the second semiconductor layer, respectively;

a source wiring on the first insulating film;

a second insulating film covering the first and second electrodes, and the source wiring;

a gate wiring on the second insulating film, the gate wiring connected to the first electrode;

a connection electrode on the second insulating film, the connection electrode connected to the source wiring and the first semiconductor layer; and

a pixel electrode on the second insulating film, the pixel electrode electrically connected to the first semiconductor layer.

49. A device according to claim 48, wherein a storage capacitor is formed by the second semiconductor layer, the second electrode, and the first insulating film.

50. A device according to claim 48, wherein:

the first semiconductor layer contains an impurity element which imparts one conductivity into the semiconductor; and

the second semiconductor layer contains an impurity element, which imparts one conductivity, opposite to that contained in the first semiconductor layer, into the semiconductor.

51. A device according to claim 48, wherein the gate wiring comprises an element selected from the group consisting of polysilicon doped with an impurity element which imparts one conductivity, W, WSix, Al, Cu, Ta, Cr, and Mo, and a lamination film of the elements.

52. A device according to claim 48, wherein the second insulating film is composed of a first insulating layer comprising silicon as its main constituent, and a second insulating layer comprising an organic resin material.

53. A device according to claim 48, wherein the semiconductor device is a reflecting type liquid crystal display device.

54. A device according to claim 48, wherein the semiconductor device is a device selected from the group consisting of a personal computer, a video camera, a portable information terminal, a digital camera, a digital video disk player, and an electronic amusement device.

55. A semiconductor device comprising:

a semiconductor layer on an insulating surface;

a first insulating film on the first semiconductor layer;

a first electrode on the first insulating film, the first electrode overlapping the first semiconductor layer;

a source wiring on the first insulating film;

a second insulating film covering the first electrode and the source wiring;

a gate wiring on the second insulating film, the gate wiring connected to the first electrode;

a connection electrode on the second insulating film, the connection electrode connected to the source wiring and the first semiconductor layer; and

a pixel electrode on the second insulating film, the pixel electrode electrically connected to the first semiconductor layer.

56. A device according to claim 55, wherein the first semiconductor layer contains an impurity element, which imparts one conductivity into the semiconductor.

57. A device according to claim 55, wherein the gate wiring comprises an element selected from the group consisting of polysilicon doped with an impurity element which imparts one conductivity, W, WSix, Al, Cu, Ta, Cr, and Mo, and a lamination film of the elements.

58. A device according to claim 55, wherein the second insulating film is composed of a first insulating layer comprising silicon as its main constituent, and a second insulating layer comprising an organic resin material.

59. A device according to claim 55, wherein at least one end of the pixel electrode overlaps with the source wiring with the second insulating film interposed therebetween.

60. A device according to claim 55, wherein the semiconductor device is a reflecting type liquid crystal display device.

61. A device according to claim 35, wherein the semiconductor device is a device selected from the group consisting of a personal computer, a video camera, a portable information terminal, a digital camera, a digital video disk player, and an electronic amusement device.

62. A semiconductor device comprising:

first and second semiconductor layers on an insulating surface;

a first insulating film on the first and second semiconductor layers;

a gate electrode and a capacitor electrode on the first insulating film, the gate electrode overlapping the first semiconductor layer and the capacitor electrode overlapping the second semiconductor layer, respectively;

a source wiring on the first insulating film;

a second insulating film covering the gate electrode, the capacitor electrode, and the source wiring;

a gate wiring on the second insulating film, the gate wiring connected to the gate electrode;

a connection electrode on the second insulating film, the connection electrode connected to the source wiring and the first semiconductor layer; and

a pixel electrode on the second insulating film, the pixel electrode electrically connected to the first semiconductor layer.

63. A device according to claim 62, wherein a storage capacitor is formed by the second semiconductor layer, the capacitor electrode, and the first insulating film.

64. A device according to claim 62, wherein:

the first semiconductor layer contains an impurity element which imparts one conductivity into the semiconductor; and

the second semiconductor layer contains an impurity element, which imparts one conductivity, opposite to that contained in the first semiconductor layer, into the semiconductor.

65. A device according to claim 62, wherein the gate wiring comprises an element selected from the group consisting of polysilicon doped with an impurity element which imparts one conductivity, W, WSix, Al, Cu, Ta, Cr, and Mo, and a lamination film of the elements.

66. A device according to claim 62, wherein the second insulating film is composed of a first insulating layer comprising silicon as its main constituent, and a second insulating layer comprising an organic resin material.

67. A device according to claim 62, wherein the semiconductor device is a reflecting type liquid crystal display device.

68. A device according to claim 62, wherein the semiconductor device is a device selected from the group consisting of a personal computer, a video camera, a portable information terminal, a digital camera, a digital video disk player, and an electronic amusement device.

69. A semiconductor device comprising:

a semiconductor layer on an insulating surface;

a first insulating film on the first semiconductor layer;

a gate electrode on the first insulating film, the gate electrode overlapping the first semiconductor layer;

a source wiring on the first insulating film;

a second insulating film covering the gate electrode and the source wiring;

a gate wiring on the second insulating film, the gate wiring connected to the gate electrode;

a connection electrode on the second insulating film, the connection electrode connected to the source wiring and the first semiconductor layer; and

a pixel electrode on the second insulating film, the pixel electrode electrically connected to the first semiconductor layer.

70. A device according to claim 69, wherein the first semiconductor layer contains an impurity element, which imparts one conductivity into the semiconductor.

71. A device according to claim 69, wherein the gate wiring comprises an element selected from the group consisting of polysilicon doped with an impurity element-which imparts one conductivity, W, WSix, Al, Cu, Ta, Cr, and Mo, and a lamination film of the elements.

72. A device according to claim 69, wherein the second insulating film is composed of a first insulating layer comprising silicon as its main constituent, and a second insulating layer comprising an organic resin material.

73. A device according to claim 69, wherein at least one end of the pixel electrode overlaps with the source wiring with the second insulating film interposed therebetween.

74. A device according to claim 69, wherein the semiconductor device is a reflecting type liquid crystal display device.

75. A device according to claim 69, wherein the semiconductor device is a device selected from the group consisting of a personal computer, a video camera, a portable information terminal, a digital camera, a digital video disk player, and an electronic amusement device.